

Title (en)  
OPTOELECTRONIC DEVICE

Title (de)  
OPTOELEKTRONISCHE VORRICHTUNG

Title (fr)  
DISPOSITIF OPTOELECTRONIQUE

Publication  
**EP 3900038 A1 20211027 (FR)**

Application  
**EP 19848783 A 20191219**

Priority  
• FR 1873944 A 20181221  
• FR 2019053176 W 20191219

Abstract (en)  
[origin: WO2020128341A1] The present description relates to an optoelectronic device (100) comprising an integrated circuit comprising light-emitting diodes (104), thin-film transistors (110) and a stack (126) of electrically insulating layers, said stack (126) being situated between the light-emitting diodes (104) and the transistors (110, 504), said stack (126) furthermore comprising conductive elements (128, 132) between and through said insulating layers, said conductive elements (128, 132) connecting at least some of the transistors to the light-emitting diodes (104).

IPC 8 full level  
**H01L 25/075** (2006.01); **H01L 25/16** (2006.01); **H01L 33/44** (2010.01)

CPC (source: EP KR US)  
**H01L 25/0753** (2013.01 - EP KR US); **H01L 25/167** (2013.01 - EP KR); **H01L 33/005** (2013.01 - US); **H01L 33/44** (2013.01 - EP KR); **H01L 33/62** (2013.01 - US); **H01L 2933/0066** (2013.01 - US)

Designated contracting state (EPC)  
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)  
BA ME

DOCDB simple family (publication)  
**WO 2020128341 A1 20200625**; CN 113383416 A 20210910; EP 3900038 A1 20211027; FR 3091027 A1 20200626; FR 3091027 B1 20221118; JP 2022515786 A 20220222; KR 20210104825 A 20210825; TW 202038427 A 20201016; US 11984549 B2 20240514; US 2022059743 A1 20220224

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**FR 2019053176 W 20191219**; CN 201980090655 A 20191219; EP 19848783 A 20191219; FR 1873944 A 20181221; JP 2021536250 A 20191219; KR 20217022446 A 20191219; TW 108146378 A 20191218; US 201917414874 A 20191219